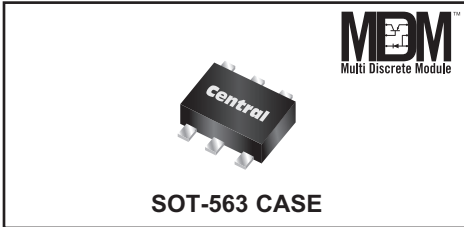


CMLM0705
MULTI DISCRETE MODULE™
SURFACE MOUNT SILICON
PNP SWITCHING TRANSISTOR AND
LOW V_F SCHOTTKY DIODE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLM0705 is a Multi Discrete Module™ consisting of a single PNP transistor and a Schottky diode packaged in a space saving SOT-563 case. This device is designed for small signal general purpose applications where size and operational efficiency are prime requirements.

- Combination: Small Signal Switching PNP Transistor and Low V_F Schottky Diode.
- Complementary Device: **CMLM2205**

MARKING CODE: C75

MAXIMUM RATINGS - CASE: (T_A=25°C)

Power Dissipation
 Operating and Storage Junction Temperature
 Thermal Resistance

SYMBOL		UNITS
P _D	350	mW
T _J , T _{stg}	-65 to +150	°C
θ _{JA}	357	°C/W

MAXIMUM RATINGS - Q1: (T_A=25°C)

Collector-Base Voltage
 Collector-Emitter Voltage
 Emitter-Base Voltage
 Continuous Collector Current

SYMBOL		UNITS
V _{CBO}	90	V
V _{CEO}	60	V
V _{EBO}	6.0	V
I _C	600	mA

MAXIMUM RATINGS - D1: (T_A=25°C)

Peak Repetitive Reverse Voltage
 Continuous Forward Current
 Peak Repetitive Forward Current, tp≤1.0ms
 Peak Forward Surge Current, tp=8.0ms

SYMBOL		UNITS
V _{RRM}	40	V
I _F	500	mA
I _{FRM}	3.5	A
I _{FSM}	10	A

ELECTRICAL CHARACTERISTICS - Q1: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{CBO}	V _{CB} =50V			10	nA
I _{CBO}	V _{CB} =50V, T _A =125°C			10	μA
I _{CEV}	V _{CE} =30V, V _{BE} =0.5V			50	nA
BV _{CBO}	I _C =10μA	90	115		V
BV _{CEO}	I _C =10mA	60			V
BV _{EBO}	I _E =10μA	5.0			V
V _{CE(SAT)}	I _C =150mA, I _B =15mA		0.113	0.2	V
V _{CE(SAT)}	I _C =500mA, I _B =50mA		0.280	0.7	V
V _{BE(SAT)}	I _C =150mA, I _B =15mA			1.3	V
V _{BE(SAT)}	I _C =500mA, I _B =50mA			2.6	V
h _{FE}	V _{CE} =10V, I _C =0.1mA	100	205		
h _{FE}	V _{CE} =10V, I _C =1.0mA	100			
h _{FE}	V _{CE} =10V, I _C =10mA	100			
h _{FE}	V _{CE} =10V, I _C =150mA	100		300	
h _{FE}	V _{CE} =10V, I _C =500mA	75	110		

R3 (1-July 2015)

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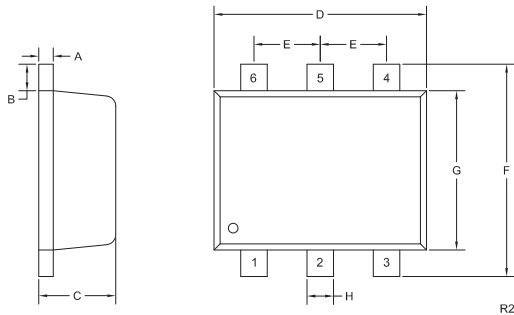
ELECTRICAL CHARACTERISTICS - Q1 - Continued:

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f _T	V _{CE} =20V, I _C =50mA, f=100MHz	200		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		8.0	pF
C _{ib}	V _{BE} =2.0V, I _C =0, f=1.0MHz		30	pF
t _{on}	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA		45	ns
t _d	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA		10	ns
t _r	V _{CC} =30V, V _{BE} =0.5V, I _C =150mA, I _{B1} =15mA		40	ns
t _{off}	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		100	ns
t _s	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		80	ns
t _f	V _{CC} =6.0V, I _C =150mA, I _{B1} =I _{B2} =15mA		30	ns

ELECTRICAL CHARACTERISTICS - D1: (T_A=25°C)

I _R	V _R =10V		20	μA
I _R	V _R =30V		100	μA
BV _R	I _R =500μA	40		V
V _F	I _F =100μA		0.13	V
V _F	I _F =1.0mA		0.21	V
V _F	I _F =10mA		0.27	V
V _F	I _F =100mA		0.35	V
V _F	I _F =500mA		0.47	V
C _J	V _R =1.0V, f=1.0MHz		50	pF

SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.059	0.067	1.50	1.70
G	0.043	0.051	1.10	1.30
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R2)

LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Cathode D1
- 4) Anode D1
- 5) Anode D1
- 6) Collector Q1

MARKING CODE: C75

R3 (1-July 2015)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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